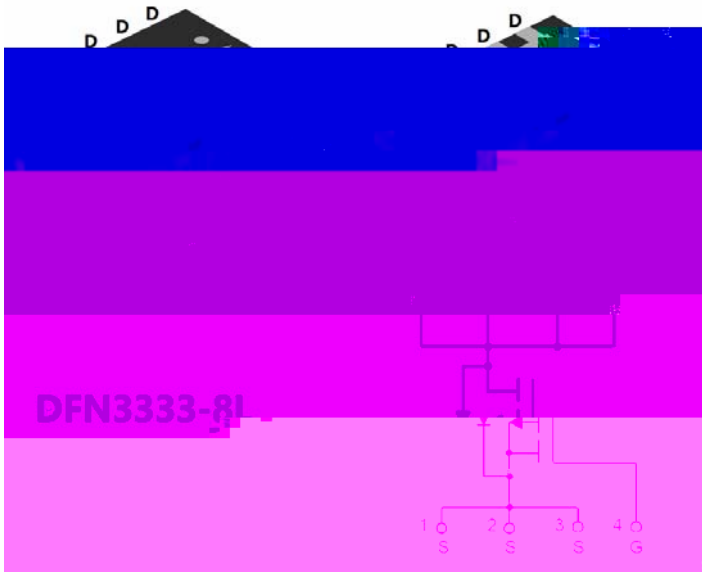




- V_{DS} -100V
- I_D -15A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) 110m Ω
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) 120m Ω
- 100% EAS Tested
- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Part no. with suffix "Q" means AEC-Q101 qualified
- Power switching application
- Uninterruptible power supply
- DC-DC convertor
- 12V, 24V and 48V Automotive systems

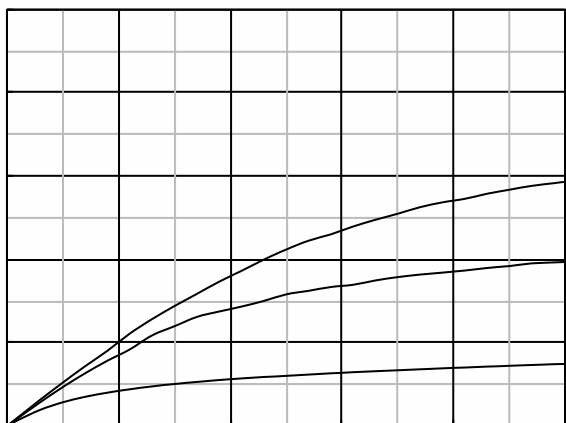
($T_A=25$ unless otherwise noted)

Drain-source Voltage		V_{DS}	-100	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25$	I_D	-3.9	A
	$T_A=100$		-2.5	
	$T_C=25$		-15	
	$T_C=100$		-9.5	
Pulsed Drain Current ^A		I_{DM}	-35	A
Avalanche energy ^B		EAS	64	mJ
Total Power Dissipation ^C	$T_A=25$	P_D	2.5	W
	$T_A=100$		1	
	$T_C=25$		43	
	$T_C=100$		17.2	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 +150	

Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	40	50	/W
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	2.4	2.9	

(Example)

YJQ15GP10AQ	F1	Q15GP10A	5000	10000	100000	13" reel



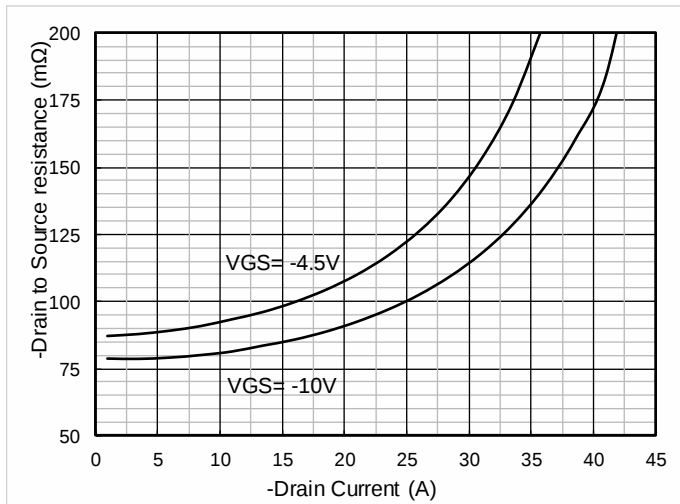


Figure 7. $R_{DS(on)}$ VS Drain Current

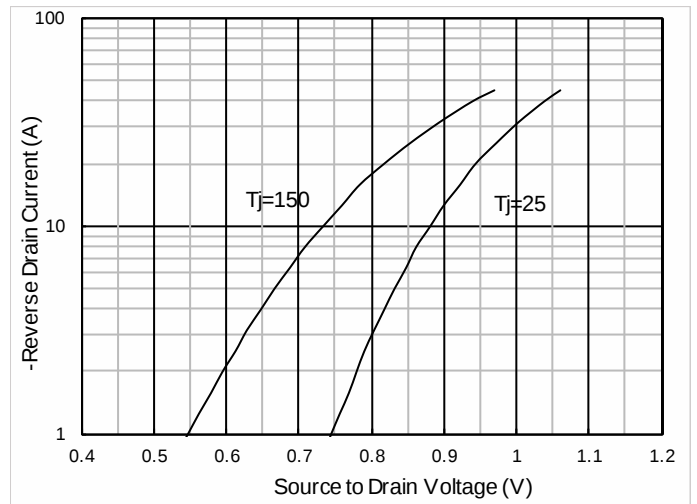


Figure 8. Forward characteristics of reverse diode

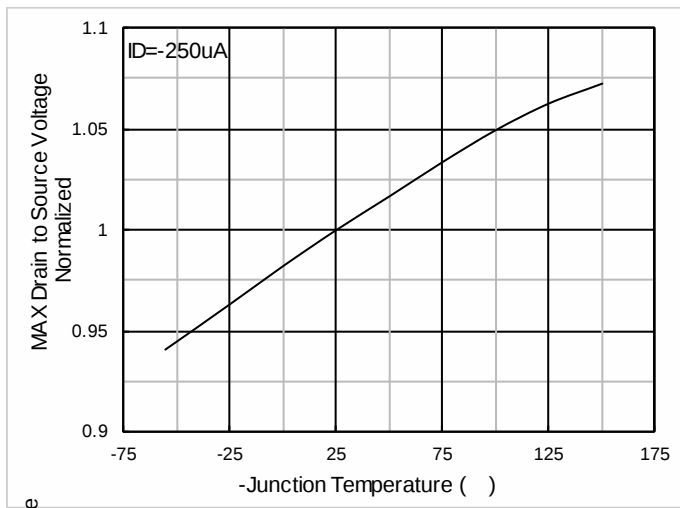


Figure 9. Normalized breakdown voltage

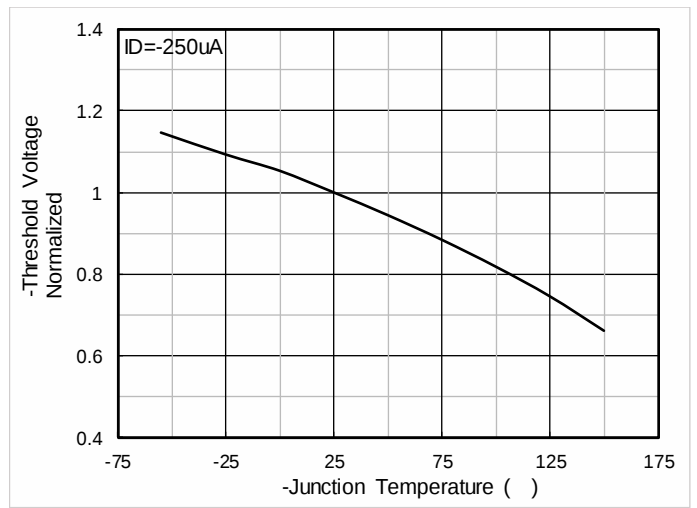


Figure 10. Normalized Threshold voltage

